

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS

1. (Withdrawn) A method of forming substantially ohmic contact regions between a layer of wide band-gap semiconductor material and contact areas disposed thereon, said method comprising: exposing said semiconductor devices to an annealing temperature less than approximately 900 degrees. Celsius for an annealing duration of greater than approximately two hours.
2. (Withdrawn) The method of claim 1, wherein said wide band-gap semiconductor material comprises a semiconductor material having a band gap of approximately two electron volts or more.
3. (Withdrawn) The method of claim 1, wherein said contact areas comprise a layer of metal or one or more portions thereof.
4. (Withdrawn) The method of claim 3, wherein said wide band-gap semiconductor material comprises silicon carbide.
5. (Withdrawn) The method of claim 4, wherein said wide band-gap semiconductor material comprises n-type silicon carbide
6. (Withdrawn) The method of claim 5, wherein said layer of metal comprises a layer of nickel.

7. (Withdrawn) The method of claim 1, wherein said annealing temperature is less than approximately 8500 Celsius and said annealing duration is greater than approximately 3 hours.

8. (Withdrawn) The method of claim 1, wherein said annealing temperature is approximately 800.degree. Celsius and said annealing duration is approximately four hours.

9. (Currently Amended) A semiconductor device, comprising:
a wide band-gap layer of n-type semiconductor material; a layer of metal disposed on at least a portion of said wide band-gap layer; and a substantially ohmic contact region between said layer of metal and said wide band-gap layer, said contact region formed by annealing said semiconductor device at an annealing temperature less than approximately 900° Celsius for an annealing duration of greater than approximately two hours.

10. (Original) The device of claim 9, wherein said wide band-gap semiconductor material comprises a semiconductor material having a band gap of approximately two electron volts or more.

11. (Original) The device of claim 10, wherein said wide band-gap semiconductor material comprises silicon carbide.

12. (Original) The device of claim 11, wherein said wide band-gap semiconductor material comprises n-type silicon carbide

13. (Original) The device of claim 10, wherein said layer of metal comprises a layer of nickel.

14. (Original) The device of claim 9, wherein said annealing temperature is less than approximately 850.degree. Celsius and said annealing duration is greater than approximately 3 hours.

15. (Original) The device of claim 9, wherein said annealing temperature is approximately 800.degree. Celsius and said annealing duration is approximately four hours.